

DOMAIN EPITAXY FOR THIN FILM GROWTH

ABSTRACT OF THE DISCLOSURE

5 A method of forming an epitaxial film on a substrate includes growing
an initial layer of a film on a substrate at a temperature T_{growth} , said initial layer
having a thickness h and annealing the initial layer of the film at a temperature
 T_{anneal} , thereby relaxing the initial layer, wherein said thickness h of the initial
layer of the film is greater than a critical thickness h_c . The method further
includes growing additional layers of the epitaxial film on the initial layer
10 subsequent to annealing. In some embodiments, the method further includes
growing a layer of the film that includes at least one amorphous island.